

- ★ Super Low Gate Charge
- ★ 100% EAS Guaranteed
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced trench gate super junction technology

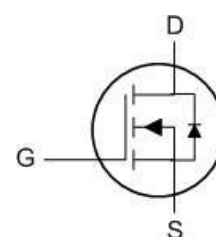
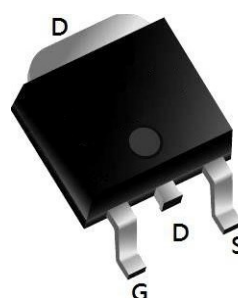
Product Summary


BVDSS	RDS(ON)	ID
700V	765mΩ	6A

Description

The XR70R750 use super junction technology and design to provide excellent RDS(ON) with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

The XR70R750 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO252-3L Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	700	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_C=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	6	A
$I_D@T_C=100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	4	A
I_{DM}	Pulsed Drain Current ²	22	A
EAS	Single Pulse Avalanche Energy ³	60	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^\circ C$	Total Power Dissipation ⁴	20	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	67	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	6.26	$^\circ C/W$

Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	700	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =1mA	---	---	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =3A	---	765	900	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	3	---	4	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	---	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =700V, V _{GS} =0V, T _J =25°C	---	---	1	uA
		V _{DS} =700V, V _{GS} =0V, T _J =100°C	---	10	---	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±30V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =20V, I _D =6A	---	5	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	9	---	Ω
Q _g	Total Gate Charge	V _{DS} =480V, V _{GS} =10V, I _D =3A	---	11	---	nC
Q _{gs}	Gate-Source Charge		---	3	---	
Q _{gd}	Gate-Drain Charge		---	4.6	---	
T _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =400V, R _G =27Ω, I _D =3A	---	13	---	ns
T _r	Rise Time		---	13	---	
T _{d(off)}	Turn-Off Delay Time		---	50	---	
T _f	Fall Time		---	61	---	
C _{iss}	Input Capacitance	V _{DS} =100V, V _{GS} =0V, f=1MHz	---	325	---	pF
C _{oss}	Output Capacitance		---	32	---	
C _{rss}	Reverse Transfer Capacitance		---	1.3	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	6	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =3A, T _J =25C	---	---	1	V
t _{rr}	Reverse Recovery Time	I _F =3A, di/dt=100A/μs,	---	185	---	nS
Q _{rr}	Reverse Recovery Charge	T _J =25 C	---	1.47	---	nC

Note :

1 The data is tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

2 The data is tested by pulsed pulse width 300us duty cycle 2%

3 The EAS data shows Max. rating. The test condition is V_{RMS}>0, V_D=200V, V_{GS}=10V, L=50mH

4 The power dissipation is limited by 150°C junction temperature

5 The data is theoretically the same as I_D and I_{DM} in real applications. It should be limited by total power dissipation.

Typical Performance Characteristics

Fig 1. Output Characteristics ($T_j=25^\circ\text{C}$)

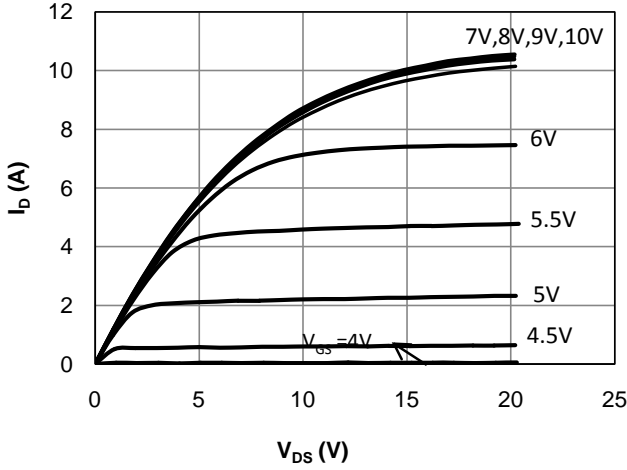


Fig 2. Output Characteristics ($T_j=150^\circ\text{C}$)

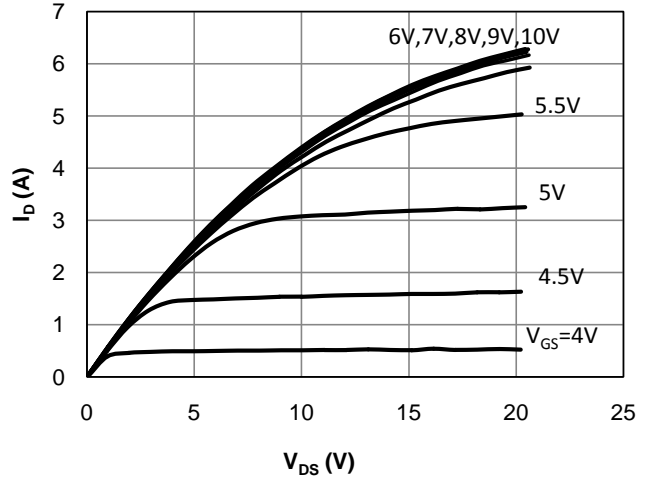


Fig 3: Transfer Characteristics

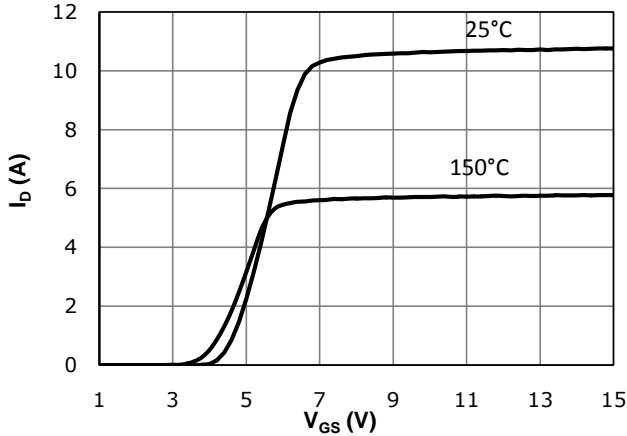


Fig 4: V_{TH} vs. T_j Temperature Characteristics

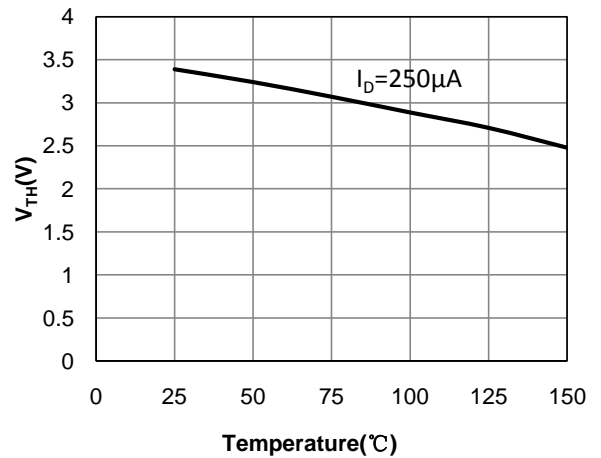


Fig 5: $R_{DS(on)}$ vs. I_{DS} Characteristics ($T_j=25^\circ\text{C}$)

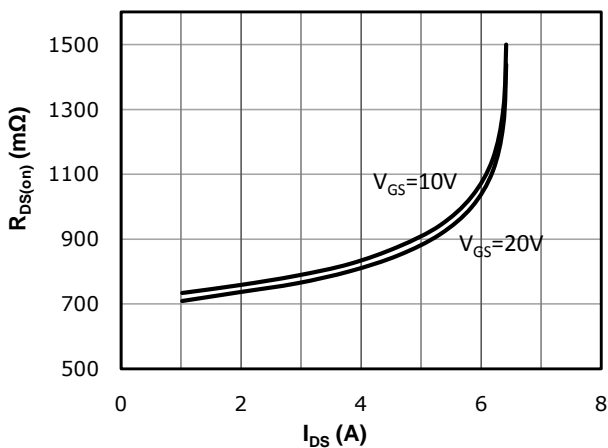


Fig 6: $R_{DS(on)}$ vs. Temperature

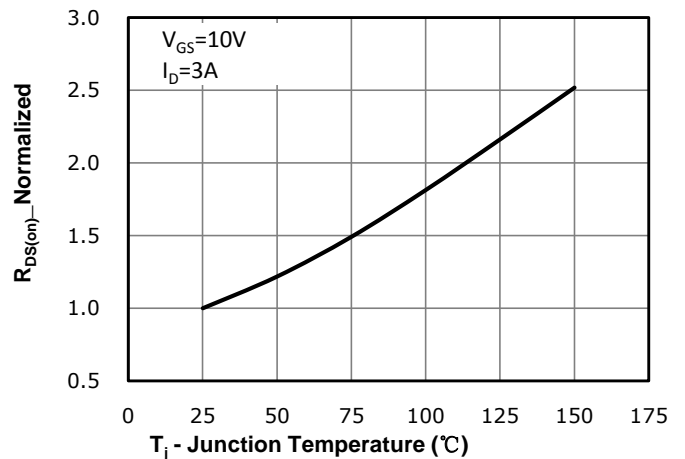


Fig 7: BV_{DSS} vs. Temperature

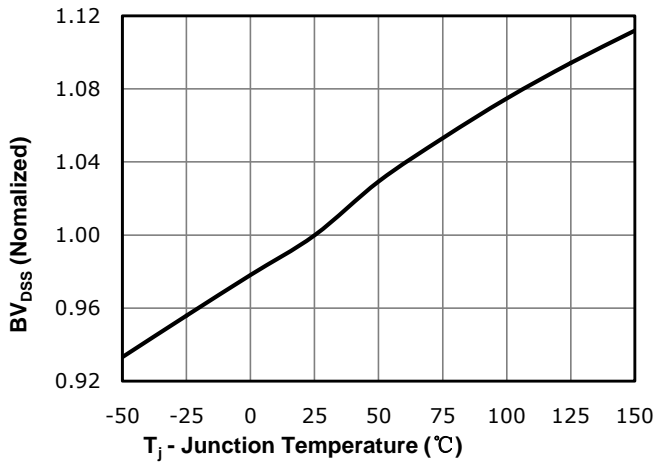


Fig 8: $R_{DS(on)}$ vs. Gate Voltage

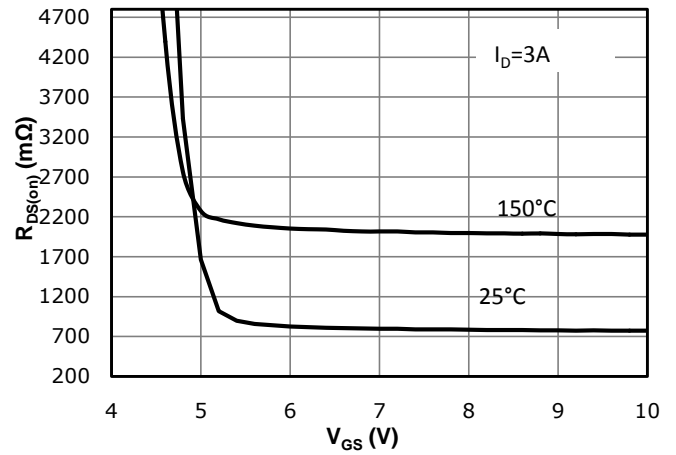


Fig 9: Body-Diode Forward Characteristics

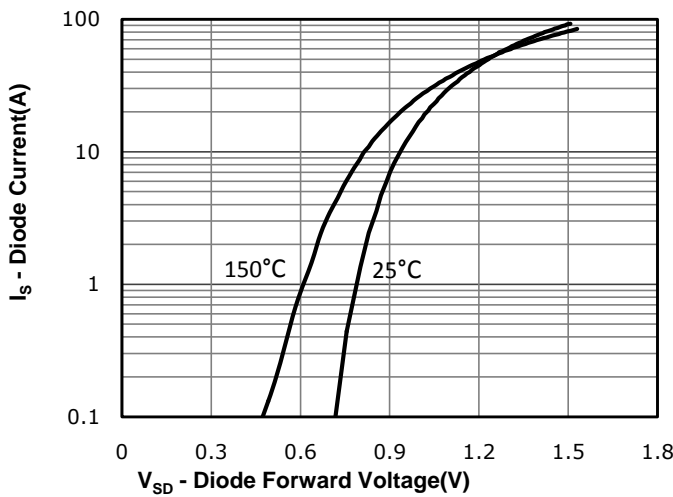


Fig 10: Gate Charge Characteristics

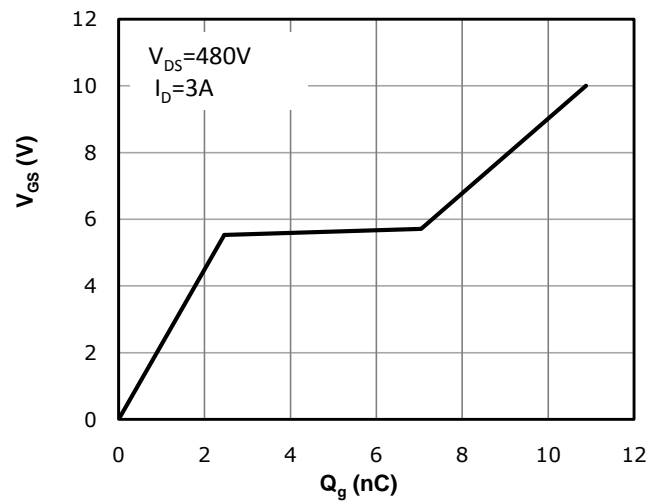


Fig 11: Capacitance Characteristics

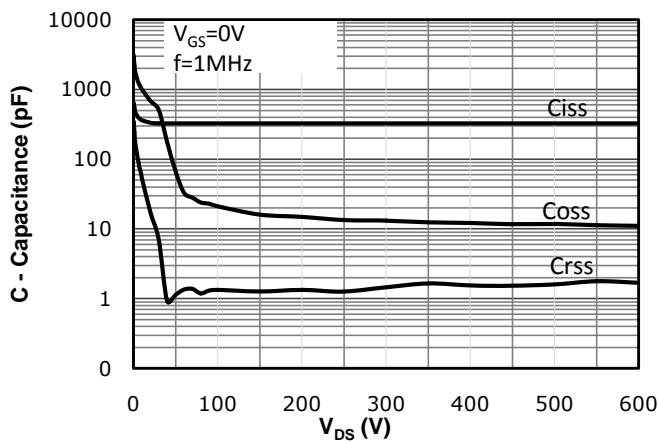


Fig 12: Safe Operating Area

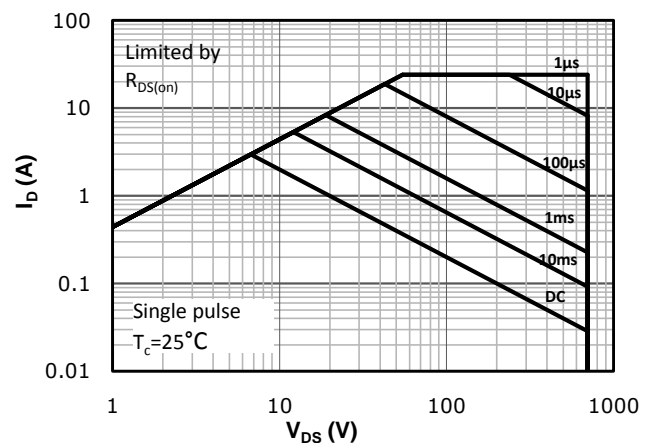
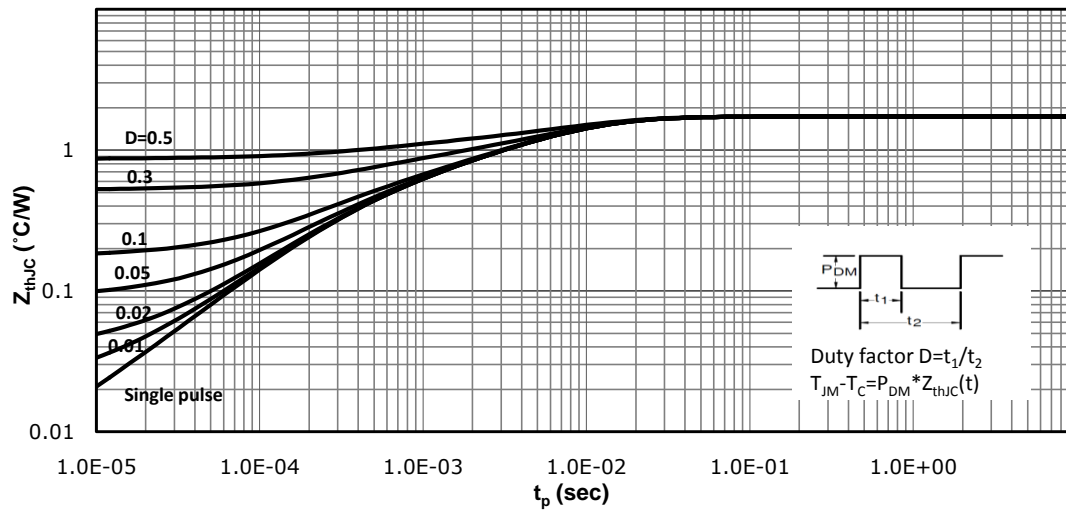
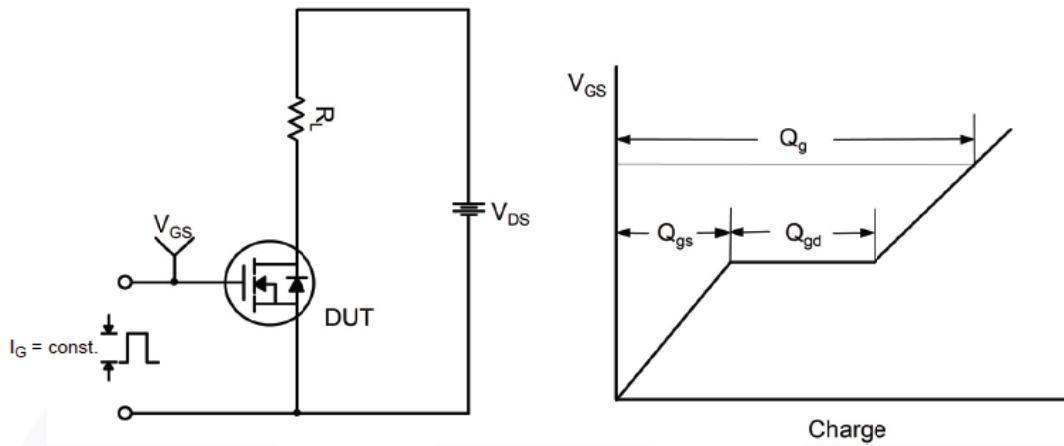


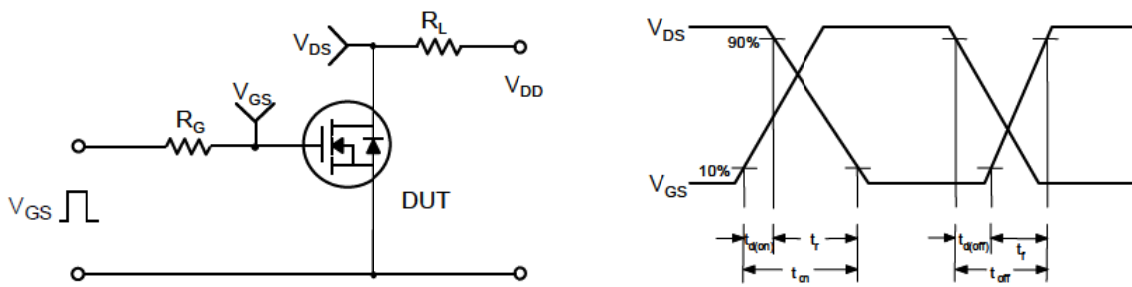
Fig 13: Max. Transient Thermal Impedance



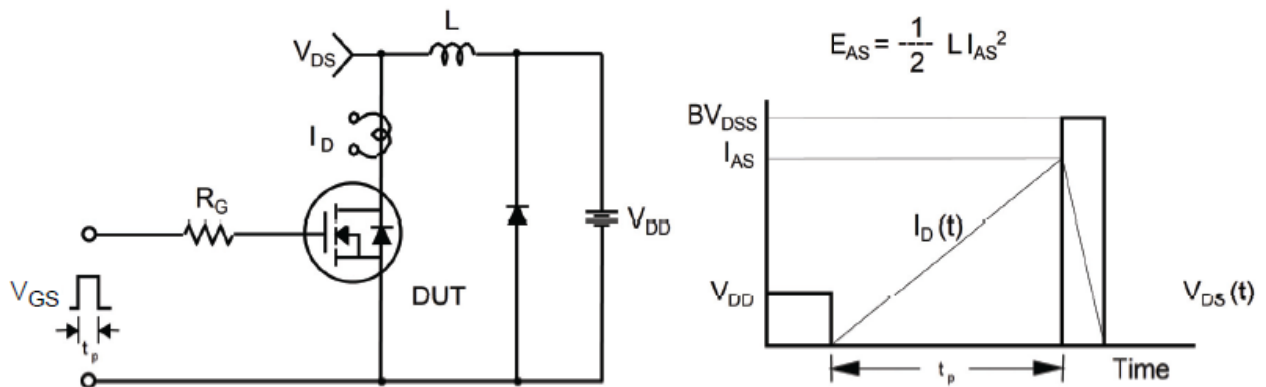
Gate Charge Test Circuit & Waveform



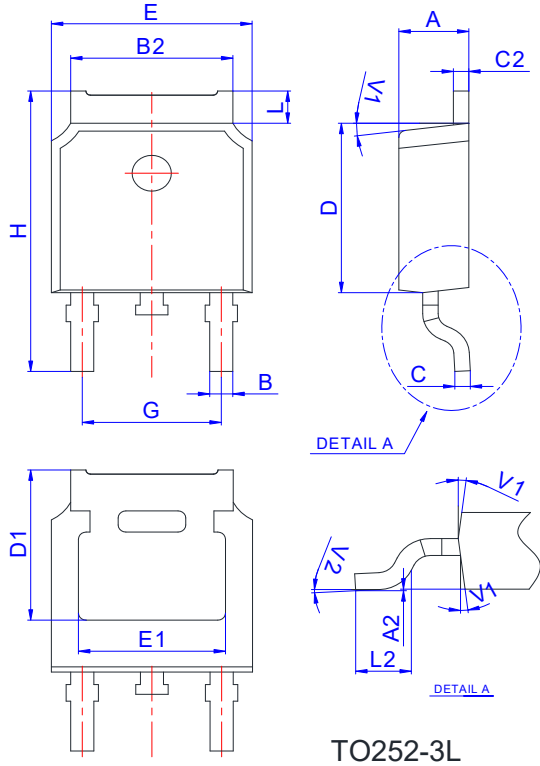
Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

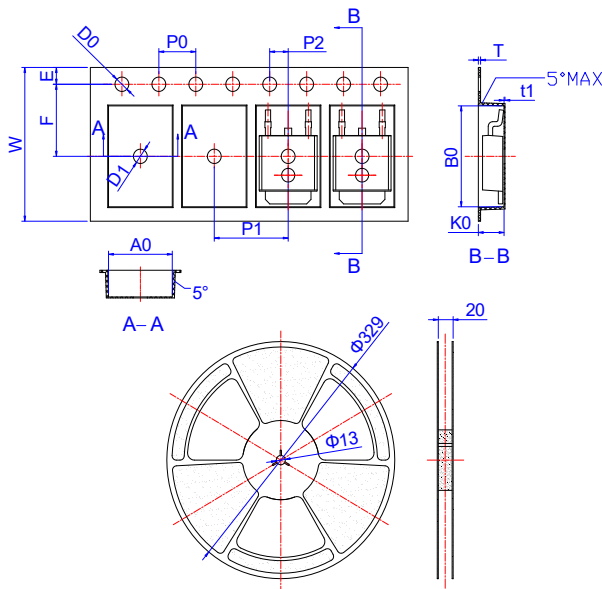


Package Mechanical Data-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Reel Specification-TO252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583